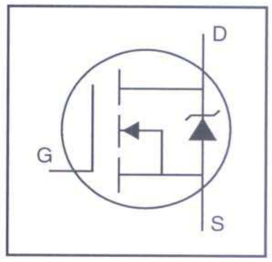
International
IOR Rectifier

PD - 96291

IRFP150MPbF

HEXFET® Power MOSFET

- Advanced Process Technology
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Lead-Free



V_{DSS} = 100V

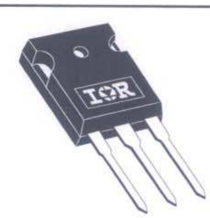
$R_{DS(on)}$ = 0.036Ω

I_D = 42A

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The TO-247 package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220 devices. The TO-247 is similar but superior to the earlier TO-218 package because of its isolated mounting hole.



TO-247AC

Absolute Maximum Ratings

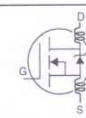
	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	42	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	30	A
I_{DM}	Pulsed Drain Current ①⑤	140	A
P_D @T_C = 25°C	Power Dissipation	160	W
	Linear Derating Factor	1.1	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy②⑤	420	mJ
I_{AR}	Avalanche Current①⑤	22	A
E_{AR}	Repetitive Avalanche Energy①	16	mJ
dv/dt	Peak Diode Recovery dv/dt ③⑤	5.0	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	°C
	Mounting torque, 6-32 or M3 srew	10 lbf•in (1.1N•m)	

Thermal Resistance

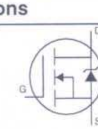
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	——	0.95	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.24	——	°C/W
$R_{\theta JA}$	Junction-to-Ambient	——	40	°C/W

03/01/10

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	—	—	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.11	—	V/°C	Reference to 25°C, I_D = 1mA⑤
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.036	Ω	V_{GS} = 10V, I_D = 23A ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	V_{DS} = V_{GS}, I_D = 250µA
g_{fs}	Forward Transconductance	14	—	—	S	V_{DS} = 25V, I_D = 22A⑤
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	µA	V_{DS} = 100V, V_{GS} = 0V
		—	—	250		V_{DS} = 80V, V_{GS} = 0V, T_J = 150°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V_{GS} = -20V
Q_g	Total Gate Charge	—	—	110	nC	I_D = 22A
Q_{gs}	Gate-to-Source Charge	—	—	15		V_{DS} = 80V
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	58		V_{GS} = 10V, See Fig. 6 and 13 ④⑤
$t_{d(on)}$	Turn-On Delay Time	—	11	—	ns	V_{DD} = 50V
t_r	Rise Time	—	56	—		I_D = 22A
$t_{d(off)}$	Turn-Off Delay Time	—	45	—		R_G = 3.6W
t_f	Fall Time	—	40	—		R_D = 2.9W, See Fig. 10 ④⑤
L_D	Internal Drain Inductance	—	5.0	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact 
L_S	Internal Source Inductance	—	13	—		
C_{iss}	Input Capacitance	—	1900	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	450	—		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	—	230	—		f = 1.0MHz, See Fig. 5⑤

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	42	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①⑤	—	—	140		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	T_J = 25°C, I_S =23A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	—	180	270	ns	T_J = 25°C, I_F = 22A
Q_{rr}	Reverse RecoveryCharge	—	1.2	1.8	µC	di/dt = 100A/µs ④ ⑤
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② Starting T_J = 25°C, L = 1.7mH R_G = 25W , I_{AS} = 22A. (See Figure 12)

③ $I_{SD} \leq$ 22A, di/dt $\leq$ 180A/µs, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq$ 175°C

④ Pulse width $\leq$ 300µs; duty cycle $\leq$ 2%.

⑤ Uses IRF1310N data and test conditions

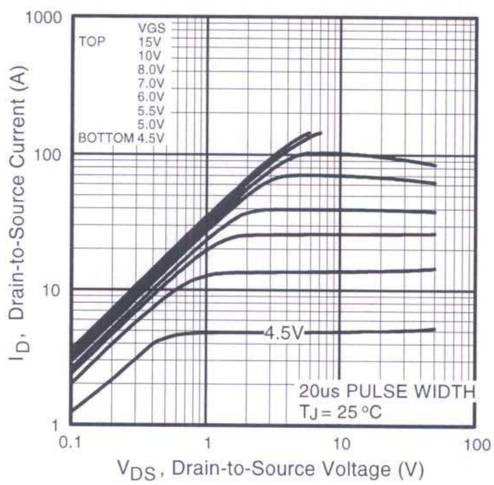


Fig 1. Typical Output Characteristics

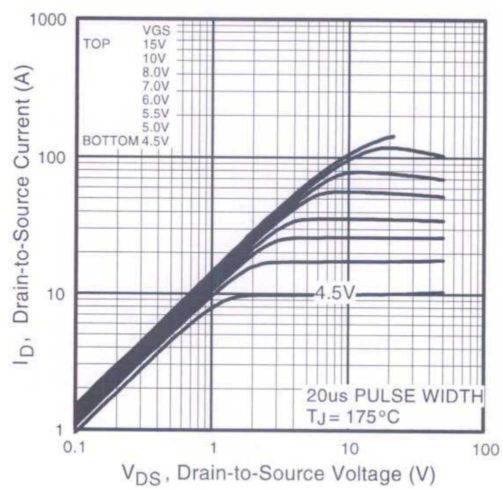


Fig 2. Typical Output Characteristics

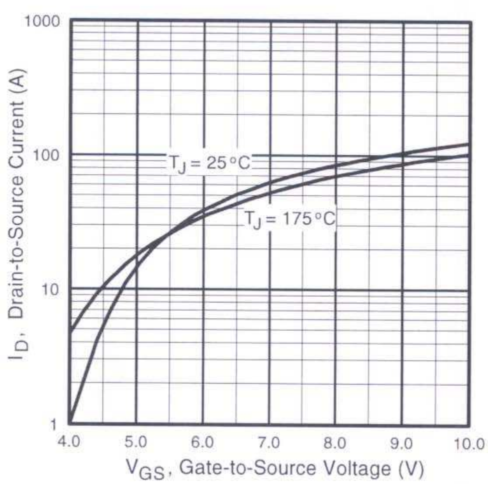


Fig 3. Typical Transfer Characteristics

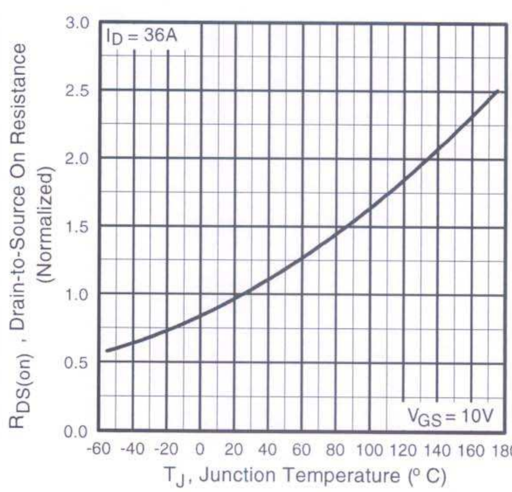


Fig 4. Normalized On-Resistance Vs. Temperature

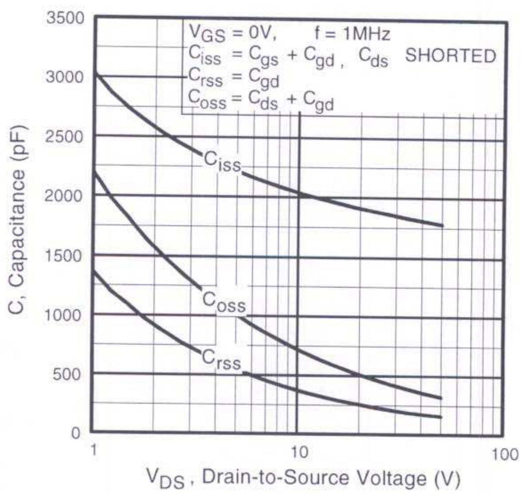


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

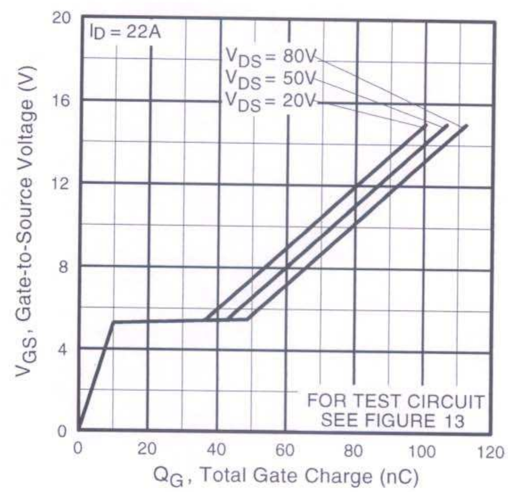


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

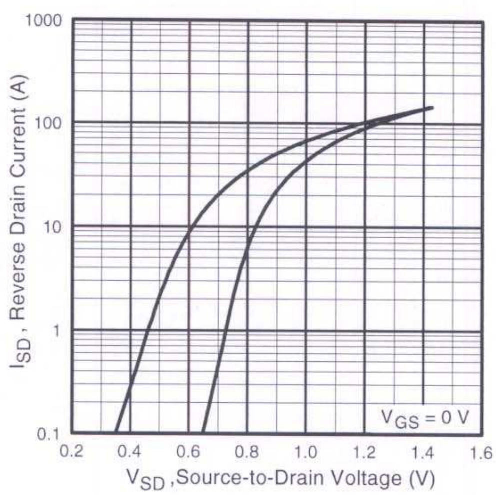


Fig 7. Typical Source-Drain Diode Forward Voltage

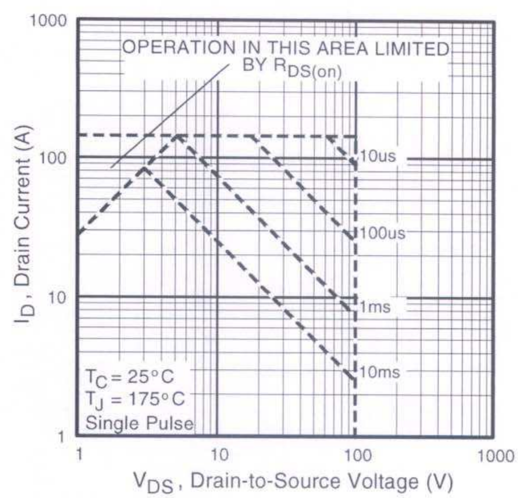


Fig 8. Maximum Safe Operating Area

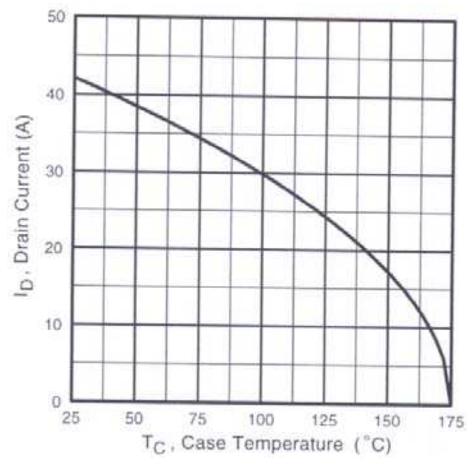


Fig 9. Maximum Drain Current Vs. Case Temperature

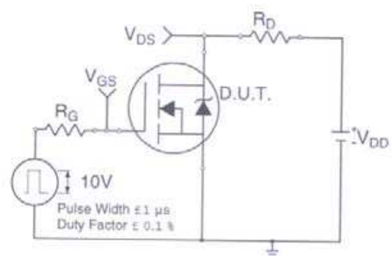


Fig 10a. Switching Time Test Circuit

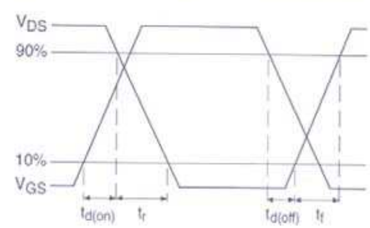


Fig 10b. Switching Time Waveforms

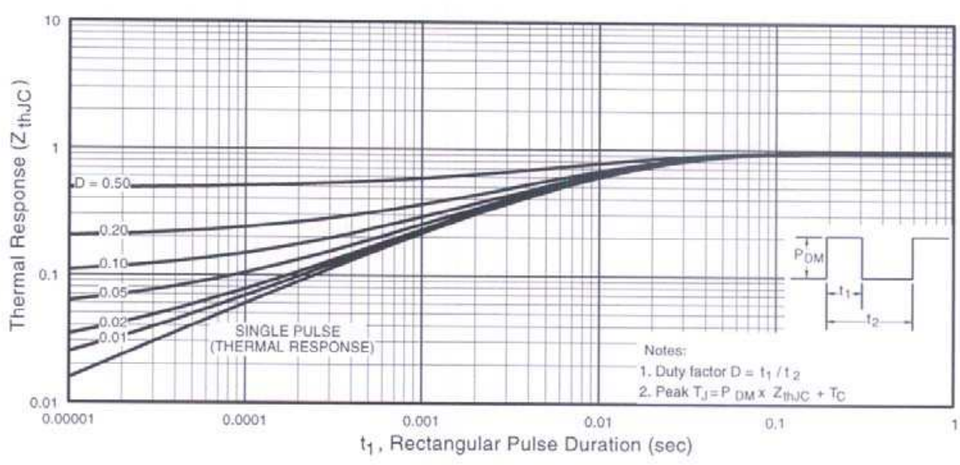


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

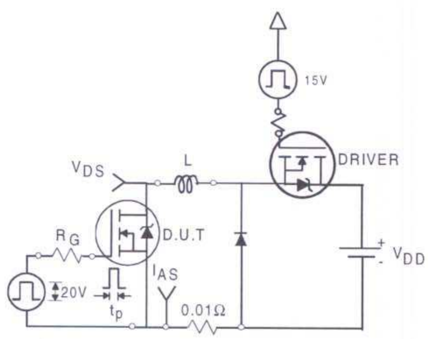


Fig 12a. Unclamped Inductive Test Circuit

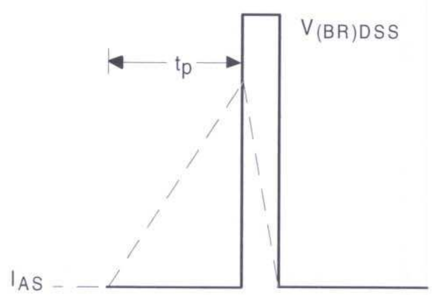


Fig 12b. Unclamped Inductive Waveforms

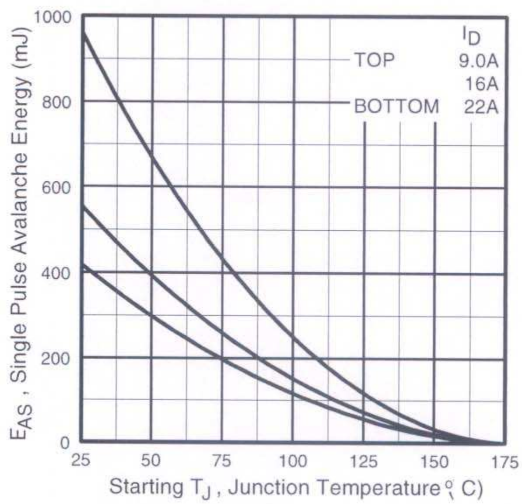


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

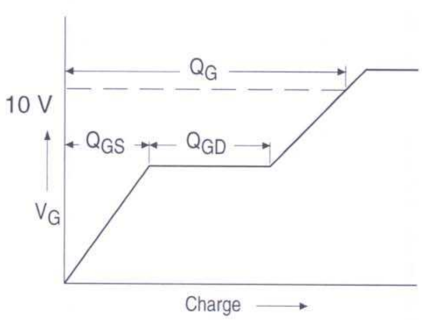


Fig 13a. Basic Gate Charge Waveform

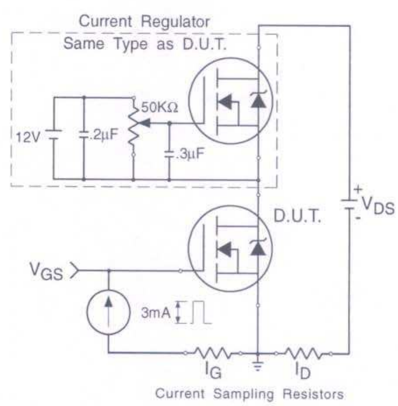


Fig 13b. Gate Charge Test Circuit

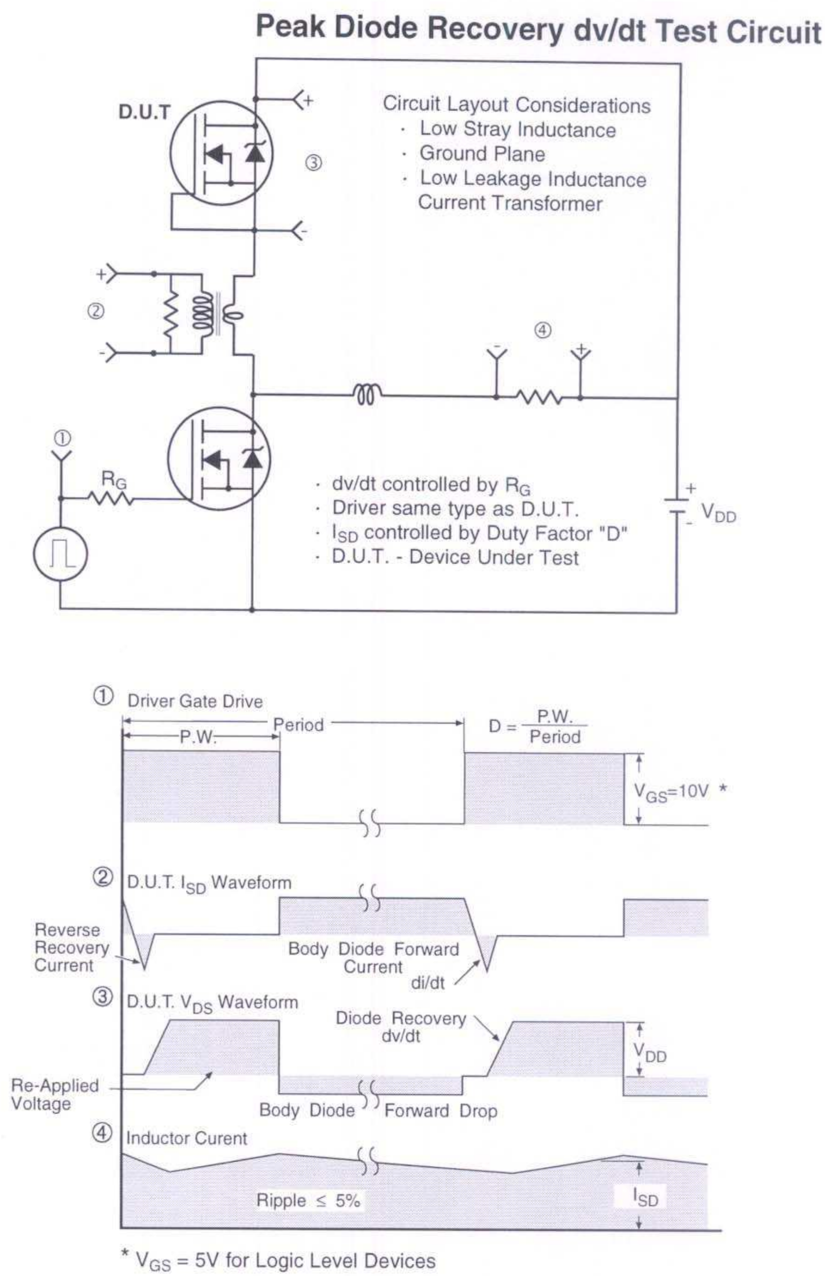
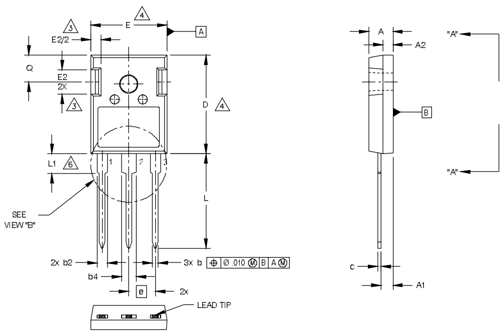


Fig 14. For N-Channel HEXFETS

TO-247AC Package Outline (Dimensions are shown in millimeters (inches))



SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.190	.204	4.83	5.20	
A1	.090	.100	2.29	2.54	
A2	.075	.085	1.91	2.16	
b	.042	.052	1.07	1.33	
b2	.075	.094	1.91	2.41	
b4	.113	.133	2.87	3.38	
c	.022	.026	0.55	0.68	
D	.819	.830	20.80	21.10	4
D1	.640	694	16.25	17.65	5
E	.620	.635	15.75	16.13	4
E1	.512	.570	13.00	14.50	
E2	.145	.196	3.68	5.00	
e	.215 Typical		5.45 Typical		
L	.780	.800	19.80	20.32	
L1	.161	.173	4.10	4.40	
ø P	.138	.143	3.51	3.65	
Q	.216	.236	5.49	6.00	
S	.238	.248	6.04	6.30	

LEAD ASSIGNMENTS

HEXFET

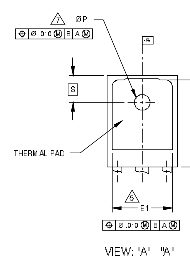
1.– GATE
2.– DRAIN
3.– SOURCE
4.– DRAIN

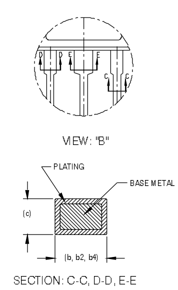
IGBTs, CoPACK

1.– GATE
2.– COLLECTOR
3.– EMITTER
4.– COLLECTOR

DIODES

1.– ANODE/OPEN
2.– CATHODE
3.– ANODE





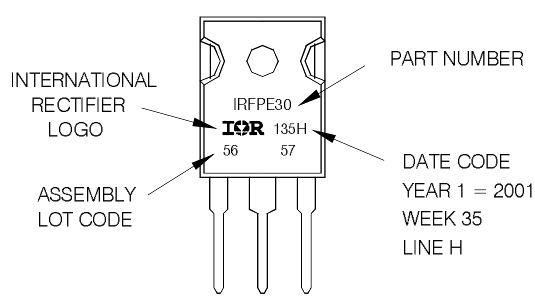
NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES AND MILLIMETERS.
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. ø P TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.

TO-247AC Part Marking Information

EXAMPLE: THIS IS AN IRFPE30
WITH ASSEMBLY
LOT CODE 5657
ASSEMBLED ON WW 35, 2001
IN THE ASSEMBLY LINE "H"

Note: "P" in assembly line position
indicates "Lead-Free"



Data and specifications subject to change without notice.

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